

isc Triacs

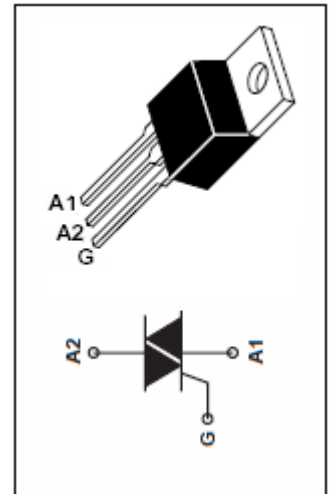
TIC226M

FEATURES

- With TO-220 package
- Sensitive Gate Triacs
- Glass Passivated
- Max I_{GT} of 50 mA (Quadrants 1~3)

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	MIN	UNIT
V_{DRM}	Repetitive peak off-state voltage	600	V
V_{RRM}	Repetitive peak reverse voltage	600	V
$I_{T(RMS)}$	RMS on-state current (full sine wave) $T_C=85^{\circ}C$	8	A
I_{TSM}	Non-repetitive peak on-state current	70	A
T_j	Operating junction temperature	110	$^{\circ}C$
T_{stg}	Storage temperature	-45~150	$^{\circ}C$
$R_{th(j-c)}$	Thermal resistance, junction to case	1.8	$^{\circ}C/W$
$R_{th(j-a)}$	Thermal resistance, junction to ambient	62.5	$^{\circ}C/W$



ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}C$ unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX	UNIT	
I_{DRM}	Repetitive peak off-state current	$V_D=V_{DRM}, T_C=110^{\circ}C$		2.0	mA	
I_{GT}	Gate trigger current	$V_{supply} = 12 V \uparrow; R_L = 10 \Omega; t_{p(g)} > 20 \mu s$	I	2	50	mA
			II	12	50	
			III	9	50	
			IV	20		
I_H	Holding current	$V_{supply} = 12 V \uparrow, I_G = 0$ initial $I_{TM}=100mA$		30	mA	
V_{GT}	Gate trigger voltage all quadrant	$V_{supply} = 12 V \uparrow; R_L = 10 \Omega; t_{p(g)} > 20 \mu s$		2	V	
V_{TM}	On-state voltage	$I_T = 12A; I_G = 50mA$		2.1	V	